

In the Specification:

Please amend the specification as follows:

The paragraph starting on page 1, line 6:

The present invention relates to a method ~~to method~~ for ~~manufacturing metal~~ manufacturing a metal line of semiconductor of a semiconductor device, and in particular to an improved method for manufacturing metal line of semiconductor device wherein undesirable etching of an edge of an interlayer insulating film which causes electrical shorts between metal lines can be prevented.

The paragraph starting on page 1, line 19:

In case of logic devices, gates and metal layers correspond to the electrical wiring layers, and contact hole layers connecting gates and metal layers and via contact hole layers connecting ~~an upper and a lower~~ upper and lower wiring layers correspond to the connection layers.

The paragraph bridging pages 2 and 3, starting on page 2, line 25:

Next, a stacked structure of a first etch barrier film 15, a second interlayer insulating film 17, a second etch barrier film 19, a third interlayer insulating film 21 and a hard mask layer 23 is formed on the entire surface. The stacked structure is then etched via a photolithography process using metal line contact mask (not shown), i.e. via contact mask (not shown) to expose the ~~first insulating film 13~~ first etch barrier film 15.

The paragraph starting on page 8, line 19:

The anti-reflection film 53, the third interlayer insulating film 51, the second etch barrier film 49 and the second interlayer insulating film 47 are etched via a photolithography process using metal line contact mask (not shown), i.e. via contact mask (not shown) to form a via contact hole 55 exposing the ~~first insulating film 45~~ first etch barrier film 45.

The paragraph bridging pages 8 and 9, starting on page 8, line 25:

Referring to Fig. 3b, the exposed portion of the ~~first insulating film 45~~ first etch barrier film 45 at the bottom of the via contact hole 55 is removed via an etching process. Portions of the anti-reflection film 53, i.e. a top and edge portions of the anti-reflection film 53 are etched in the etching process of the ~~first insulating film 45~~ first etch barrier film 45. As a result, the thickness of the anti-reflection film 53 is reduced and the edge portion of the anti-reflection film 53 at the top corner of the via contact hole 55 is etched to have a shape denoted as 'B' in Fig. 3b.

The paragraph starting on page 10, line 8:

Referring to Fig. 3e, the portion of the photoresist film pattern 59 in the via contact hole 55 is removed preferably by performing an in-situ plasma-etching process using a mixture gas of $\text{CF}_4/\text{O}_2/\text{Ar}$. The remaining portion of the photoresist film pattern 59 is then removed. Edge portions of the ~~anti-reflection film 52~~ anti-reflection film 53 and the second etch barrier film 49 in the upper metal line region 61, which are denoted as 'C' in Fig. 3e, are not etched.